


Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 10559-586002	Application No. 10/802,331
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)		Applicant Lawrence D. Wong	
		Filing Date March 16, 2004	Group Art Unit 2826
(37 CFR §1.98(b))			

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
Sw	AA	4,848,141	07-1989	Oliver et al.	73	81	
Sw	AB	6,340,628	01-2002	Van Cleemput et al.	438	586	
	AC						
	AD						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
	AE						Yes	No
	AF							
	AG							

Other Documents (Include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
Sw	AH	Hara et al., "Mechanism of Mechanical and Chemical Polishing in Low Dielectric Constant Plasma-Enhanced Chemical Vapor Deposition SiOC Layer from hexamethyldisiloxane", Electrochem. And Solid State Lett., 4(8):65-67 (Aug. 2001).
	AI	Masic et al., "Synthesis and Mechanical Properties of Boron Suboxide Thin Films", J. Vac. Sci. Technol. A, 20(2):335-337 (Apr. 2002).
	AJ	Liu, P.T. et al., "The Effects of Plasma Treatment for Low Dielectric Constant Hydrogen Silsesquioxane (HSQ)", Thin Solid Films v. 332, pgs. 345-350 (1998).
	AK	Kondoh, E., "Structural Change in Porous Silica Thin Film after Plasma Treatment", Electrochem. and Solid-State Lett., 1(5):224-226 (1998).
	AL	Gidley et al., "Determination of pore-Size Distribution in Low-Dielectric Thin Films", App. Phys. Lett., 76(10):1282-1284 (2000).
	AM	Loboda et al., "Using Trimethylsilane to Improve Safety, Throughput and Versatility in PECVD Processes", Electrochem. Proc., 97(10):443-453.
	AN	Loboda et al., "Deposition of Low-K Dielectric Films Using Trimethylsilane", Proc. Of the Symposium on Electrochem. Proc. In ULSI Fabrication and Interconnect and Contact Metallization: Materials, Processes and Reliability, pgs. 145-152 (1998).
	AO	Sugahara et al., "Low Dielectric Constant Carbon Containing SiO <sub>2</sub> Films Deposited by PECVD Techniques Using a Novel CVD Precursor", Int'l. Dielectrics for ULSI Multilevel Interconnection Conference, pgs. 19-25 (1997).
Sw	AP	Kanaya et al., "Penetration and Energy-Loss Theory of Electrons in Solid Targets", J. Phys. D.: Appl. Phys., vol. 5, pgs. 43-58 (1972).

Examiner Signature 	Date Considered 7/5/2007
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	